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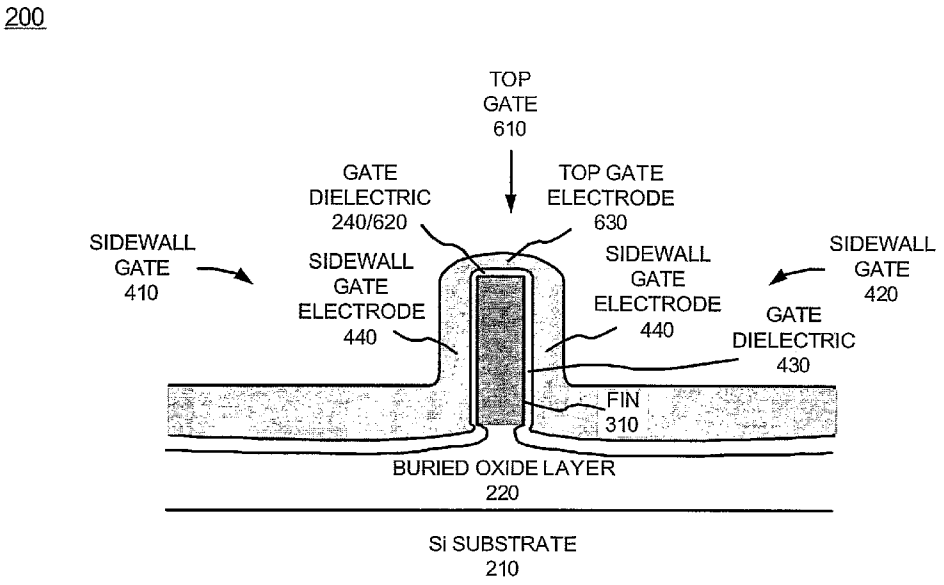
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(54) Title: TRI-GATE AND GATE AROUND MOSFET DEVICES AND METHODS FOR MAKING SAME




(57) Abstract: A triple gate metal-oxide semiconductor field-effect transistor (MOSFET) (200) includes a fin structure (310), a first gate (410) formed adjacent a first side of the fin structure (310), a second gate (420) formed adjacent a second side of the fin structure (310) opposite the first side, and a top gate (610) formed on top of the fin structure (310). A gate around MOSFET (800) includes multiple fins (1110), a first sidewall gate structure (1010) formed adjacent one of the fins (l 110), a second sidewall gate structure (1020) formed adjacent another one of the fins (1110), a top gate structure (1230) formed on one or more of the fins (1110), and a bottom gate structure (1240) formed under one or more of the fins (1110).

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